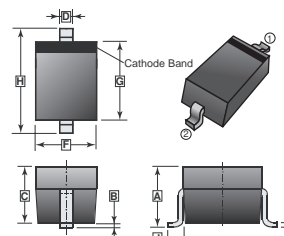


RoHS Compliant Product
 A suffix of "-C" specifies halogen & lead-free

FEATURES

- Low turn-on voltage
- Fast switching
- Microminiature plastic package
- This device is protected by a PN junction guard ring against excessive voltage, such as electrostatic discharge.
- Ideal for protection of MOS device, steering, Biasing, and coupling diodes for fast switching and Low logic level applications.

SOD-323



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	1.05	REF.	E	0.080	0.180
B	0.20	REF.	F	1.15	1.45
C	0.80	1.00	G	1.60	1.80
D	0.25	0.40	H	2.30	2.70

MARKING : S21

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS, Single Diode at T_A = 25°C

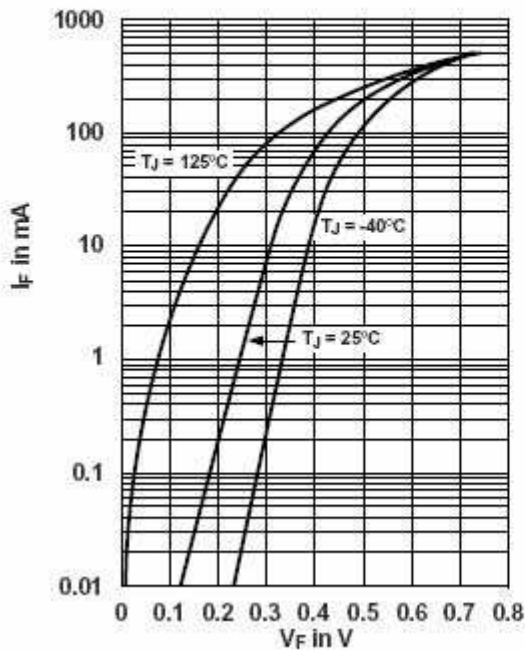
PARAMETER	SYMBOL	RATINGS	UNIT
Non-Repetitive Peak reverse voltage	V _{RM}	30	V
Forward Current	I _{FM}	200	mA
Forward Surge Current (t _p =10ms)	I _{FSM}	1	A
Power Dissipation (T _C =25°C)	P _{TOT}	250	mW
Thermal Resistance Junction to Ambient Air	T _{θJA}	500	°C/W
Junction, Storage Temperature	T _J , T _{STG}	150, -65~150	°C

ELECTRICAL RATING at T_A = 25°C

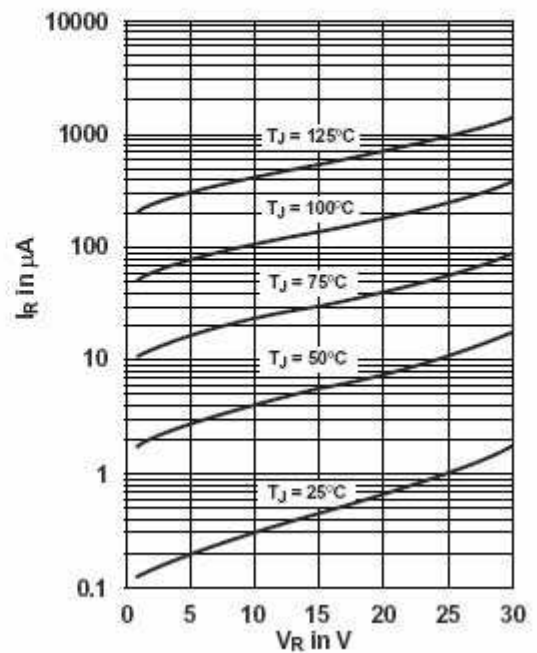
PARAMETERS	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Reverse Breakdown Voltage	V _R	30			V	I _R = 100µA
Forward Voltage	V _F		260		mV	I _F = 2mA
			320			I _F = 15mA
			420			I _F = 100mA
			490	550		I _F = 200mA
Reverse Current	I _R			5	µA	V _R = 30V
Capacitance between Terminals	C _T			15	pF	V _R = 10V, f = 1MHZ

RATINGS AND CHARACTERISTIC CURVES

Forward Voltage Forward Current at Various Temperatures (Typical Values)



Typical Variation of Reverse Current at Various Temperatures



Typical Capacitance $^\circ\text{C}$ vs. Reverse Applied Voltage V_R

